IN THE CLAIMS

The following is a listing of the claims in the application, with claims 1 and 5 shown as amended and claims 6 and 7 cancelled.

LISTING OF CLAIMS

1. (Currently Amended) A method for preparing a film structure of a ferroelectric single crystal, which comprises adhering a ferroelectric single crystal plate to a substrate by a conductive adhesive ~~or metal layer~~ , wherein the ferroelectric single crystal is a material having the composition of formula (I):

x(A)y(B)z(C)-p(P)n(N) (I)

wherein

is Pb(Mg1/3Nb2/3)03 or Pb(Zn1/3Nb2/3)03,

is PbTiO3,

is LiTa03,

(P) is a metal selected from the group consisting of Pt, Au, Ag, Pd and Rh,

(N) is an oxide of a metal selected from the group consisting of Ni, Co, Fe, Sr, Sc, Ru, Cu and Cd,

x is a number in the range of 0.65 to 0.98,

y is a number in the range of 0.01 to 0.34,

z is a number in the range of 0.01 to 0.1, and

p and n are each independently a number in the range of 0.01 to 5,

wherein the conductive adhesive is a gold- or silver- containing epoxy paste, or a Pt-containing adhesive sol.

2. (Previously Amended) The method of claim 1, wherein the single crystal plate is polished to a thickness of 1 to 100 pm before or after the adhesion with the substrate.

3. (Original) The method of claim 1, wherein the single crystal plate is adhered to the substrate by placing a conductive adhesive between the single crystal plate and the substrate and heat treating the resulting laminate containing the adhesive at a temperature ranging from room temperature to 150 °C for Ito 24 hours to cure the adhesive.

4. (cancelled)

5. (currently amended) The method of claim [3] 1, wherein the adhesive is applied using terminal portion made of an elastic rubber.

6. (cancelled)

7. (cancelled)

8. (Original) The method of claim 1, wherein the ferroelectric single crystal has a dielectric constant of 1,000 or greater as measured in a film form.

9. (Cancelled)

10. (Original) The method of claim 1, wherein the substrate comprises a layer of an oxide material selected from SiO2, MgO, Al203 and ZnO, the oxide layer being co ntacted with the conductive adhesive layer.

11. (Original) The method of claim 1, which further comprises forming a conductive metal layer on the surface of the single crystal plate opposite to the adhesive layer by a sputtering or an electronic beam evaporation method.

12. (Previously Amended) A ferroelectric single crystal film structure prepared by a method according to claim 1.

13. (Original) An electric or electronic device comprising the ferroelectric single crystal film structure according to claim 12.